

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

**Applicant(s):** Robert H. Dennard, et al.      **Examiner:** Unassigned  
**Serial No.:** To be assigned      **Art Unit:** Unassigned  
**Filed:** Herewith      **Docket:** YOR920020157US2(15667A)  
**For:** POLYSILICON BACK-GATED      **Dated:** September 11, 2003  
SOI MOSFET FOR DYNAMIC THRESHOLD  
VOLTAGE CONTROL

Commissioner for Patents  
United States Patent and Trademark Office  
P.O. Box 1450  
Alexandria, VA 22313-1450

**PRELIMINARY AMENDMENT**

Sir:

In connection with filing the above-identified patent application under 37 C.F.R. §1.53(b), applicants submit the following amendments and remarks for entry of record in the above-identified patent application.

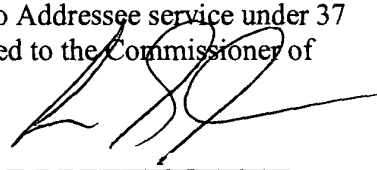
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Dated: September 11, 2003

  
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Leslie S. Szivos, Ph.D.